

**FEATURES**

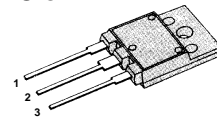
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 25  $\mu$ A (Max.) @  $V_{DS} = 800V$
- Low  $R_{DS(on)}$  : 0.746  $\Omega$  (Typ.)

$$BV_{DSS} = 800 V$$

$$R_{DS(on)} = 0.95 \Omega$$

$$I_D = 6.5 A$$

**TO-3PF**



1.Gate 2. Drain 3. Source

**Absolute Maximum Ratings**

Symbol	Characteristic	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	800	V
$I_D$	Continuous Drain Current ( $T_C=25^\circ C$ )	6.5	A
	Continuous Drain Current ( $T_C=100^\circ C$ )	4.1	
$I_{DM}$	Drain Current-Pulsed	40	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy	518	mJ
$I_{AR}$	Avalanche Current	6.5	A
$E_{AR}$	Repetitive Avalanche Energy	10	mJ
dv/dt	Peak Diode Recovery dv/dt	2.0	V/ns
$P_D$	Total Power Dissipation ( $T_C=25^\circ C$ )	100	W
	Linear Derating Factor	0.8	
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	- 55 to +150	$^\circ C$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

**Thermal Resistance**

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta_{JC}}$	Junction-to-Case	--	1.25	$^\circ C/W$
$R_{\theta_{JA}}$	Junction-to-Ambient	--	40	

### Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$BV_{DSS}$	Drain-Source Breakdown Voltage	800	--	--	V	$V_{GS}=0V, I_D=250\ \mu\text{A}$
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	1.02	--	V/°C	$I_D=250\ \mu\text{A}$ <b>See Fig 7</b>
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	3.5	V	$V_{DS}=5V, I_D=250\ \mu\text{A}$
$I_{GSS}$	Gate-Source Leakage, Forward	--	--	100	nA	$V_{GS}=30V$
	Gate-Source Leakage, Reverse	--	--	-100		$V_{GS}=-30V$
$I_{DSS}$	Drain-to-Source Leakage Current	--	--	25	$\mu\text{A}$	$V_{DS}=700V$
		--	--	250		$V_{DS}=560V, T_C=125^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.95	$\Omega$	$V_{GS}=10V, I_D=3A$ *
$g_{fs}$	Forward Transconductance	--	6.6	--	$\Omega$	$V_{DS}=50V, I_D=3A$
$C_{iss}$	Input Capacitance	--	2700	3500	pF	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$ <b>See Fig 5</b>
$C_{oss}$	Output Capacitance	--	260	300		
$C_{rss}$	Reverse Transfer Capacitance	--	110	130		
$t_{d(on)}$	Turn-On Delay Time	--	29	70	ns	$V_{DD}=350V, I_D=6A,$ $R_G=11.5\Omega$ <b>See Fig 13</b>
$t_r$	Rise Time	--	58	125		
$t_{d(off)}$	Turn-Off Delay Time	--	152	315		
$t_f$	Fall Time	--	48	105		
$Q_g$	Total Gate Charge	--	125	165	nC	$V_{DS}=560V, V_{GS}=10V,$ $I_D=6A$ <b>See Fig 6 &amp; Fig 12</b>
$Q_{gs}$	Gate-Source Charge	--	19.2	--		
$Q_{gd}$	Gate-Drain(Filler") Charge	--	55.4	--		

### Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$I_S$	Continuous Source Current	--	--	6.5	A	Integral reverse pn-diode in the MOSFET
$I_{SM}$	Pulsed-Source Current	--	--	40		
$V_{SD}$	Diode Forward Voltage	--	--	1.4	V	$T_J=25^\circ\text{C}, I_S=6A, V_{GS}=0V$
$t_{rr}$	Reverse Recovery Time	--	620	--	ns	$T_J=25^\circ\text{C}, I_F=6A$
$Q_{rr}$	Reverse Recovery Charge	--	10.17	--	$\mu\text{C}$	$di_F/dt=100A/\mu\text{s}$

#### Notes ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ②  $L=23\text{mH}, I_{AS}=6.5A, V_{DD}=50V, R_G=27\Omega,$  Starting  $T_J=25^\circ\text{C}$
- ③  $I_{SD}\leq 6A, di/dt\leq 200A/\mu\text{s}, V_{DD}\leq BV_{DSS},$  Starting  $T_J=25^\circ\text{C}$
- ④ Pulse Test : Pulse Width = 250  $\mu\text{s}$ , Duty Cycle  $\leq 2\%$
- ⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

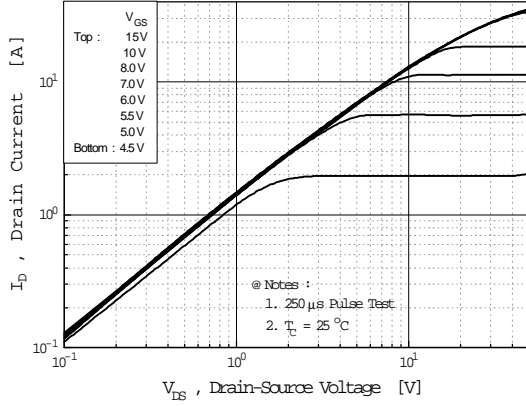


Fig 2. Transfer Characteristics

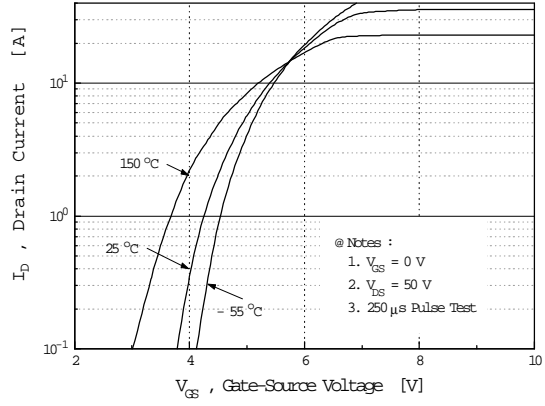


Fig 3. On-Resistance vs. Drain Current

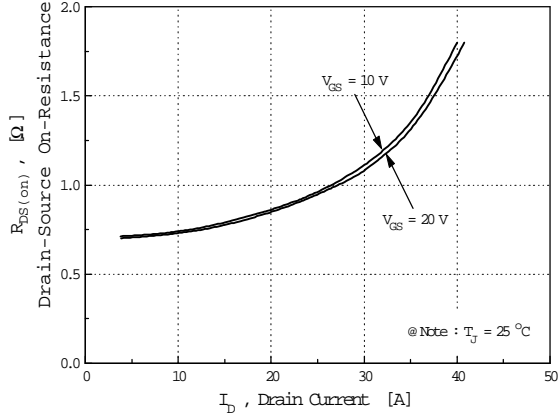


Fig 4. Source-Drain Diode Forward Voltage

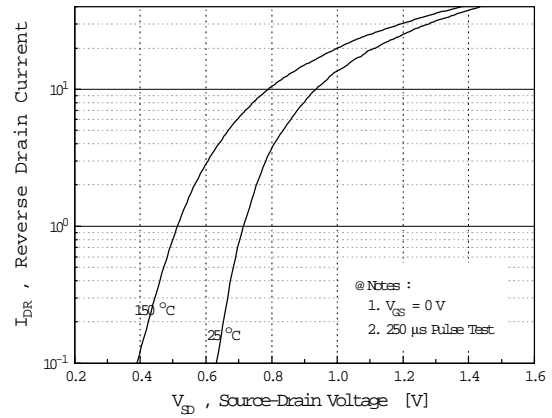


Fig 5. Capacitance vs. Drain-Source Voltage

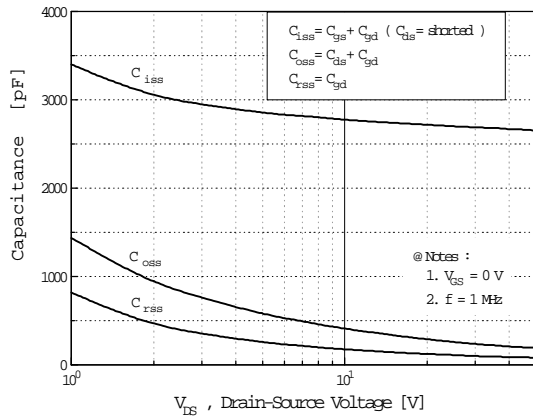
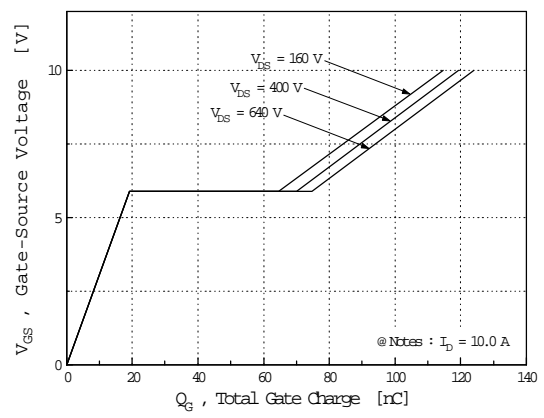


Fig 6. Gate Charge vs. Gate-Source Voltage



# SSF10N80A

## N-CHANNEL POWER MOSFET

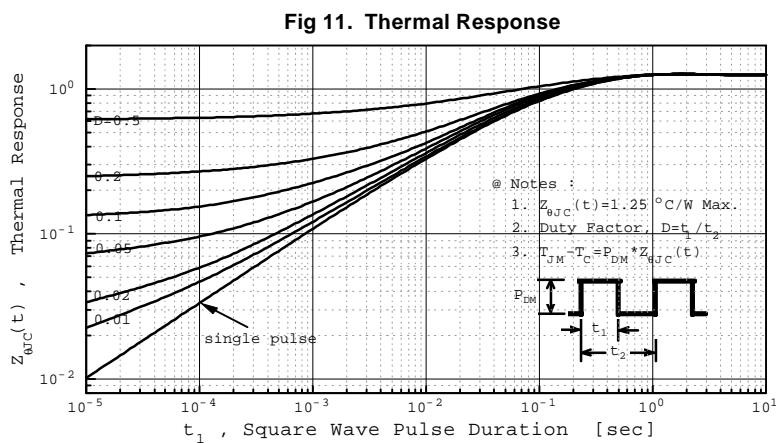
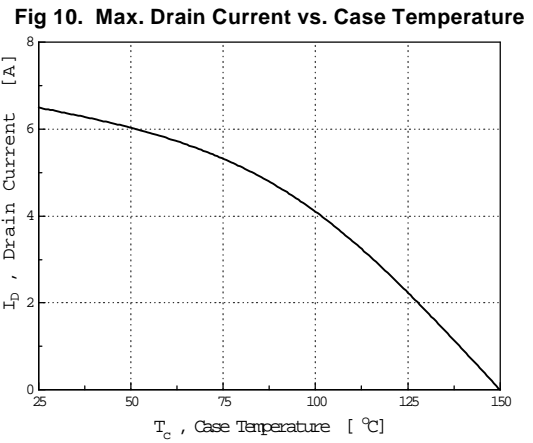
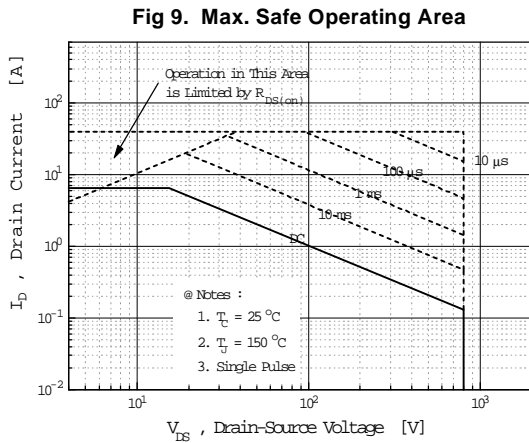
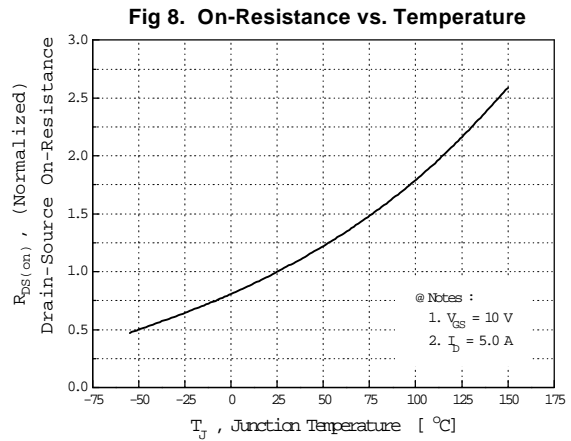
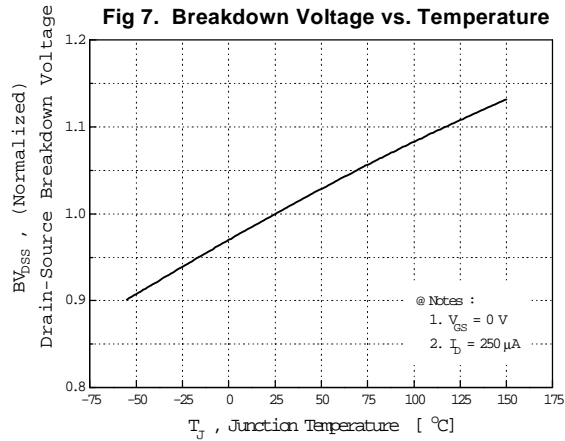


Fig 12. Gate Charge Test Circuit & Waveform

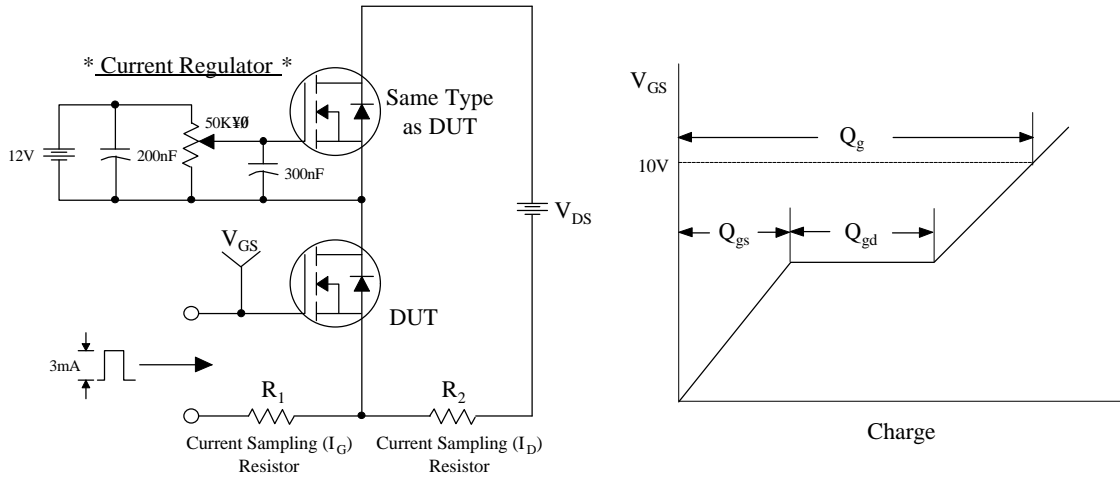


Fig 13. Resistive Switching Test Circuit & Waveforms

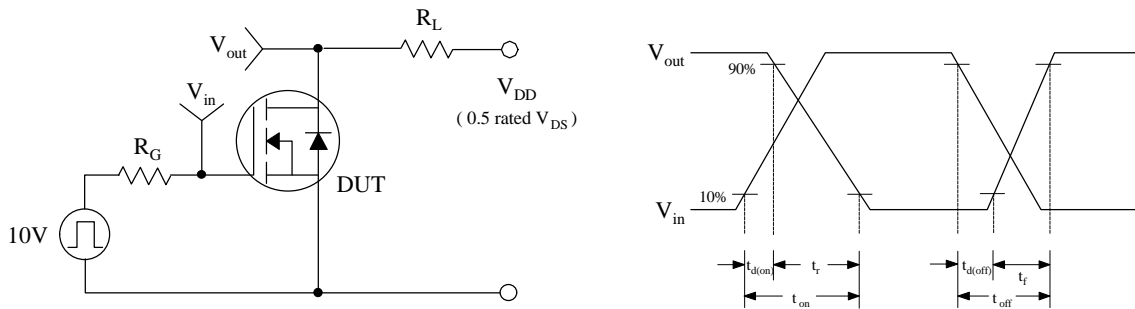


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

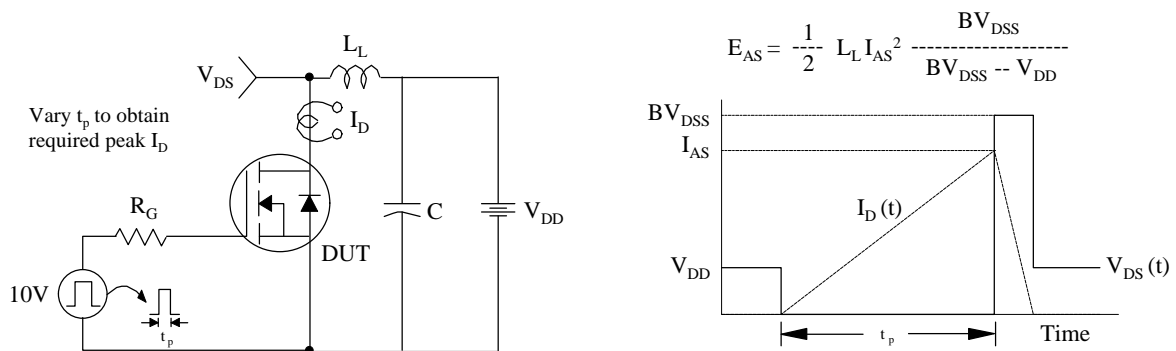
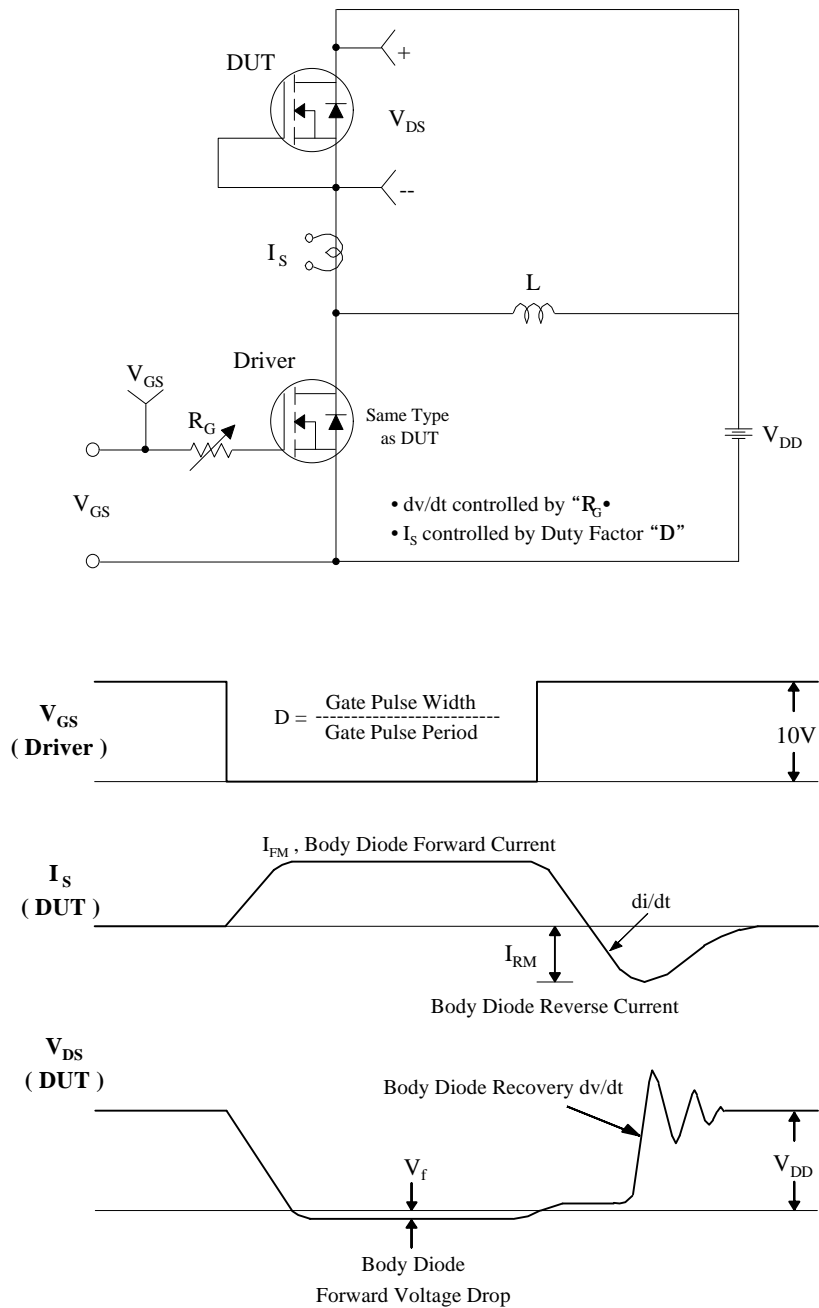


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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